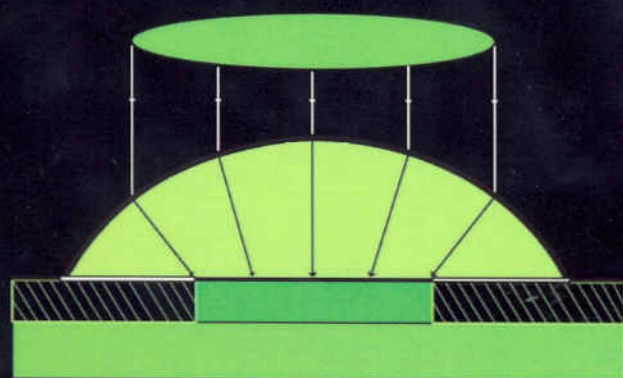


High-Operating- Temperature Infrared Photodetectors

Jozef Piotrowski

Antoni Rogalski



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Contents

Acronyms and Abbreviations / ix

Preface / xi

Chapter 1 Introduction / 1

- 1.1 General Remarks / 1
- 1.2 Detector Figures of Merit / 5
 - 1.2.1 Responsivity / 5
 - 1.2.2 Noise equivalent power / 6
 - 1.2.3 Detectivity / 6
- 1.3 Detectivity Requirements for Thermal Imagers / 8
- 1.4 Cooling of IR Detectors / 10
 - 1.4.1 Cryogenic dewars / 12
 - 1.4.2 Joule-Thompson coolers / 12
 - 1.4.3 Stirling cycle coolers / 12
 - 1.4.4 Peltier coolers / 13
- References / 13

Chapter 2 Fundamental Performance Limitations of Infrared Photodetectors / 15

- 2.1 Infrared Photon Detector Classifications / 15
- 2.2 Theoretical Model / 16
 - 2.2.1 Optical generation noise / 18
 - 2.2.1.1 Noise due to optical signal / 18
 - 2.2.1.2 Noise due to background radiation / 18
 - 2.2.1.3 Internal radiative generation / 20
 - 2.2.2 Thermal generation and recombination noise / 21
- 2.3 Optimum Thickness of a Detector / 21
- 2.4 Detector Material Figure of Merit / 23
- 2.5 Reducing Device Volume to Enhance Performance / 24
 - 2.5.1 Enhancing absorption / 24
 - 2.5.2 Increasing the apparent "optical" area of a detector compared to its physical area / 25
- References / 29

Chapter 3 Materials Used for Intrinsic Photodetectors / 33

- 3.1 Semiconductors for Intrinsic Photodetectors / 34
- 3.2 $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ Ternary Alloys / 35
 - 3.2.1 Band structure and electrical properties / 35
 - 3.2.1.1 Band structure / 35
 - 3.2.1.2 Intrinsic concentration / 36
 - 3.2.1.3 Mobilities / 37
 - 3.2.2 Defects and impurities / 38
 - 3.2.2.1 Native defects / 38
 - 3.2.2.2 Dopants / 40
 - 3.2.3 Growth of bulk crystals and epilayers / 40
 - 3.2.3.1 Phase diagrams / 41
 - 3.2.3.2 Bulk crystals / 42
 - 3.2.3.3 Epitaxy / 43
- 3.3 Hg-based Alternatives to HgCdTe / 47
 - 3.3.1 Crystal growth / 48
 - 3.3.2 Physical properties / 49
- 3.4 InAs/Ga_{1-x}In_xSb Type II Superlattices / 52
- 3.5 Novel Sb-Based Materials / 55
 - 3.5.1 InAsSb / 55
 - 3.5.2 InTlSb and InTlP / 57
 - 3.5.3 InSbBi / 58
 - 3.5.4 InSbN / 58
- 3.6 Lead Salts / 59
 - 3.6.1 Physical properties / 60
 - 3.6.2 Deposition of polycrystalline PbS and PbSe films / 62
- References / 63

Chapter 4 Intrinsic Photodetectors / 75

- 4.1 Optical Absorption / 75
- 4.2 Thermal Generation-Recombination Processes / 80
 - 4.2.1 Shockley-Read processes / 81
 - 4.2.2 Internal radiative processes / 82
 - 4.2.3 Auger processes / 83
- 4.3 Auger-Dominated Performance / 85
 - 4.3.1 Equilibrium devices / 85
 - 4.3.2 Nonequilibrium devices / 87
- 4.4 Modeling of High-Temperature Photodetectors / 91
- References / 94

Chapter 5 $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ Photoconductors / 99

- 5.1 Simplified Model of Equilibrium Mode Photoconductors / 99
 - 5.1.1 High-frequency operation of photoconductors / 102
 - 5.1.2 $10.6\text{-}\mu\text{m}$ $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ photoconductor operating at $200\text{--}300\text{ K}$ / 103
- 5.2 Excluded Photoconductors / 106
- 5.3 Practical Photoconductors / 109
 - 5.3.1 Technology of $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ photoconductors / 109
 - 5.3.1.1 Practical excluded photoconductors / 111
 - 5.3.1.2 Optically immersed photoconductors / 112
 - 5.3.1.3 Detector housing / 114
 - 5.3.2 Measured performance / 115
 - 5.3.2.1 Near room temperature devices / 115
 - 5.3.2.2 Low-temperature devices / 117
 - 5.3.2.3 Excluded photoconductors / 118
- 5.4 SPRITE Detectors / 119
- References / 123

Chapter 6 $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ Photodiodes / 129

- 6.1 Theoretical Design of $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ Photodiodes / 129
 - 6.1.1 Photocurrent and dark current of photodiodes / 129
 - 6.1.2 Structures of $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ photodiodes / 130
 - 6.1.3 Current-voltage characteristics of photodiodes / 137
 - 6.1.4 Quantum efficiency issues of high-temperature photodiodes / 145
 - 6.1.5 Frequency response of $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ photodiodes / 147
- 6.2 Technology of $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ Photodiodes / 148
 - 6.2.1 Basic configurations of photodiodes / 148
 - 6.2.2 Junction formation / 150
 - 6.2.2.1 Hg in-diffusion / 150
 - 6.2.2.2 Ion implantation / 150
 - 6.2.2.3 Ion milling / 151
 - 6.2.2.4 Reactive ion etching / 151
 - 6.2.2.5 Doping during growth / 151
 - 6.2.2.6 Other techniques / 152
 - 6.2.3 Passivation / 152
 - 6.2.4 Contact metallization / 153
- 6.3 Practical Photodiodes / 153
 - 6.3.1 SWIR photodiodes / 153
 - 6.3.2 MWIR photodiodes / 153
 - 6.3.3 LWIR photodiodes / 158
 - 6.3.4 Practical stacked multiple-cell devices / 162
 - 6.3.5 Auger-suppressed photodiodes / 163
- References / 169

Chapter 7 Photoelectromagnetic, Magnetoconcentration, and Dember IR Detectors / 179

- 7.1 PEM Detectors / 179
 - 7.1.1 PEM effect / 179
 - 7.1.1.1 Transport equations in a magnetic field / 180
 - 7.1.1.2 Life solution / 181
 - 7.1.2 Practical HgCdTe PEM detectors / 185
 - 7.1.2.1 Fabrication / 185
 - 7.1.2.2 Measured performance / 186
- 7.2 Magnetoconcentration Detectors / 187
- 7.3 Dember Detectors / 190
- References / 194

Chapter 8 Lead Salt Photodetectors / 197

- 8.1 PbS and PbSe Photoconductors / 198
 - 8.1.1 Fabrication / 198
 - 8.1.2 Performance / 200
- 8.2 Lead Salt Photovoltaic Detectors / 204
- References / 208

Chapter 9 Alternative Uncooled Long-Wavelength IR Photodetectors / 211

- 9.1 HgZnTe and HgMnTe Detectors / 211
- 9.2 III-V Detectors / 214
- 9.3 InAs/Ga_{1-x}In_xSb Type-II Superlattice Detectors / 220
- 9.4 Thermal Detectors / 222
- References / 228

Chapter 10 Final Remarks / 233

- 10.1 Summary of Progress to Date / 233
- 10.2 Directions for Future Development / 233
- References / 235

Index / 237

Index

α /G ratio, 23

A

- absorption coefficient, 21
 - extrinsic, 3
 - hyperbolic model, 79
 - intrinsic, 3
 - Kane model, 76
 - of HgCdTe, 75
 - Urbach tail, 77
- alternative substrates, 44
- anodic oxidation, 111
- Auger mechanism, 83

B

- background-limited performance, 18
- background radiance, 19
- blackbody photon flux density, 18
- bolometers, 1, 223
 - focal plane arrays, 225
 - principle of operation, 3

C

- carrier mobility
 - in HgCdTe, 394
 - in InSb, 328
 - in lead salts, 525
- coolers, 10
 - Joule-Thompson coolers, 11
 - Stirling coolers, 12
 - thermoelectric coolers, 13
- current transport, 93
 - for electrons, 93
 - for holes, 93
 - Poisson's equation, 93

D

- dark current, 130, 139
- Dember detectors, 190
 - multiple-cell device, 194
 - voltage responsivity, 191
- detectivity, 6, 17, 21
 - limited by Auger 1 process, 86
 - limited by Auger 7 process, 86
 - of photodetectors, 21, 23
 - of photodiodes, 135

detectors

- comparison of detectors, 4
- Dember detectors, 190
- extrinsic, 3, 15
- intrinsic, 3, 15
- PEM detectors, 178
- photoconductive detectors, 100
- photoemissive detectors, 3
- photon detectors, 1
- photovoltaic detectors, 4, 129
- pyroelectric detectors, 1
- quantum well infrared photodetectors, 3
- SPRITE detectors, 119
- semiconductor materials, 34
- theoretical model, 16
- thermal detectors, 1

E

- excluded photoconductor, 106, 118
- extrinsic absorption, 3
- extrinsic detectors, 3

F

- field of view, 19
- flux density, 18
- f /number, 8
- focal plane arrays, 8
 - bolometers, 225
 - HgCdTe, 167
 - lead salts, 204
- frequency response, 147

G

- generation, 18
 - generation-recombination processes, 18, 80
 - optical generation, 18
 - radiative generation, 20
 - thermal generation, 18

H

- HgCdTe ternary alloys, 35
 - band structure, 35
 - effective masses, 37
 - intrinsic concentration, 36
 - mobilities, 37
 - physical properties, 36

- HgCdTe crystal growth, 40
 - bulk crystals, 42
 - dopants, 40
 - epitaxial layers, 43
 - phase diagrams, 41
 - native defects, 38
 - HgCdTe Demer detectors, 192
 - HgCdTe junction formation, 150
 - doping during growth, 151
 - Hg-in diffusion, 150
 - ion implantation, 150
 - ion milling, 151
 - reactive ion etching, 151
 - HgCdTe magnetoconcentration detectors, 187
 - HgCdTe photoconductors, 99
 - current responsivity, 100
 - detectivity, 103
 - detector housing, 114
 - excluded photoconductor, 106, 118
 - low-temperature devices, 117
 - noise, 101
 - model, 99
 - nonequilibrium devices, 87
 - optically immersed photoconductors, 112
 - passivation, 110
 - performance, 115
 - preparation, 109
 - room temperature devices, 115
 - SPRITE detectors, 119
 - HgCdTe photodiodes, 129
 - Auger-suppressed photodiodes, 163, 167
 - band diagram, 138
 - basic configurations, 148
 - contact metallization, 153
 - current-voltage characteristics, 137
 - dark current, 133
 - detectivity, 135
 - frequency response, 147
 - fundamental limitations, 135
 - ion implantation, 150
 - ion milling, 151
 - LWIR photodiodes at low temperatures, 158
 - MWIR photodiodes, 154
 - noise, 135
 - nonequilibrium photodiodes, 163
 - n-p homojunction, 132
 - n^+ -p homojunction, 132
 - n^+ -i-p structure, 140
 - N^+ -p- P^+ structure, 143
 - N^+ -p- N^+ structure, 149
 - passivation, 152
 - photocurrent, 129
 - preparation, 150
 - proximity-extracting photodiode, 163
 - R_0A product, 136, 155
 - SWIR photodiodes, 153
 - triple-layer heterojunction, 133
 - HgCdTe PEM detectors, 182
 - fabrication, 185
 - theory, 178
 - HgCdTe properties, 35
 - absorption coefficient, 76
 - Auger process, 83
 - band structure, 37
 - carrier lifetime, 80
 - carrier mobilities, 38
 - defects, 38
 - dopants, 40
 - energy gap, 36
 - generation-recombination mechanisms, 80
 - intrinsic concentration, 36
 - minority carrier lifetimes, 82
 - radiative process, 82
 - Schockley-Read process, 81
 - HgZnTe detectors, 211
 - HgZnTe ternary alloys, 47
 - crystal growth, 48
 - physical properties, 49
 - HgMnTe ternary alloys, 47
 - crystal growth, 48
 - physical properties, 50
 - HgMnTe detectors, 211
 - PEM detectors, 214
 - photodiodes, 213
 - HOTEYE camera, 168
- I**
- immersion, 26
 - hyperimmersion lens, 27
 - immersion lens, 26, 114
 - InAs/GaInSb strained layer superlattices, 51
 - band gap diagram, 52
 - carrier lifetime, 54
 - physical properties, 53
 - InAs/GaInSb strained layer superlattice
 - detectors, 220
 - photodiodes, 221
 - photoconductors, 222
 - performance, 223
 - InAsSb ternary alloy, 55
 - crystal growth, 56
 - physical properties, 55
 - InAsSb photodiodes, 215
 - InSbBi detectors, 217
 - InSb/InAlSb photodiodes, 218
 - interdiffused multilayer process, 45
 - interference effects, 24
 - intrinsic photodetectors, 75
 - isothermal vapour phase epitaxy, 45
- L**
- lead salts, 59
 - crystal growth, 60
 - deposition of polycrystalline films, 61

effective masses, 60
 physical properties, 59
 lead salt focal plane arrays, 202
 lead salt photodetectors, 197
 configuration, 200
 performance, 200
 polycrystalline films, 190
 preparation, 198
 lead salt photodiodes, 204
 liquid phase epitaxy, 44

M

magnetoconcentration detectors, 187
 metalorganic chemical vapor deposition, 45
 molecular beam epitaxy, 44
 multiple-heterojunction device, 146, 148, 161

N

narrow-gap semiconductors, 32
 noise equivalent temperature difference, 8
 noise equivalent power, 6
 noise mechanisms
 generation-recombination noise, 21, 101
 in photoconductors, 101
 in photodiodes, 135
 Johnson-Nyquist noise, 101
 $1/f$ noise, 101
 noise voltage, 7
 nonequilibrium devices, 87
 detectivity, 89
 novel Sb-based materials, 55
 InTlSb and InTiP, 57
 InSbBi, 58
 InSbN, 58

O

optical generation, 18
 optical immersion, 27
 hemispherical immersion, 26
 hyperhemispherical immersion, 26
 optically immersed photoconductors, 112
 optically immersed Demer detector, 193
 optically immersed photodiodes, 161

P

passivation, 110, 152
 PbS photoconductive detectors, 198
 detectivity, 201
 fabrication, 198
 focal plane arrays (FPAs), 202
 performance, 201
 PbSe photoconductive detectors, 198
 detectivity, 201
 fabrication, 198
 focal plane arrays (FPAs), 202
 performance, 201
 PbSe photodiodes, 205
 PbTe photodiodes, 205

PEM detectors, 179
 detectivity, 182
 fabrication, 185
 responsivity, 183
 measured performance, 186
 PEM effect, 180
 Lile model, 181
 photoconductors, 99
 noise mechanism, 101
 nonequilibrium devices, 87
 sweep-out effect, 101
 ultimate performance, 20
 photocurrent, 133
 photoelectrical gain, 17, 102
 photodetectors, 17
 general theory, 17
 modeling, 91
 photodiodes, 129
 configurations, 148
 dark current, 137
 fabrication, 150
 noise, 135
 passivation, 152
 quantum efficiency, 145
 R_0A product, 135
 physical properties
 HgCdTe, 36
 HgMnTe, 49
 HgZnTe, 49
 InAsSb, 326
 lead salts, 521
 Poisson's equation, 92
 pyroelectric detectors, 1

Q

quantum efficiency, 17, 145
 quantum well infrared photodetectors, 4

R

R_0A product, 135
 recombination mechanisms, 81
 Auger 1, 84
 Auger 7, 84
 Auger process, 83
 radiative process in HgCdTe, 82
 Shockley-Read process in HgCdTe, 81
 refractive index, 20, 24
 resonant cavity, 24, 145
 responsivity, 5
 blackbody responsivity, 6
 current responsivity, 17
 voltage responsivity, 5

S

SPRITE detectors, 119
 principle of operation, 120
 performance, 122

strained layer superlattice detectors, 220
 InAsSb/InSb, 215
 InAs/GaInSb, 220
 versus HgCdTe, 222

T

thermal detectors, 1
 bolometers, 1, 224
 costs, 226

thermal figure of merit, 8
thermal generation, 21
time-delay integration, 120

V

van Roosbroeck model, 93

W

Winston cone, 29